## IN THE CLAIMS

Please amend claims 2, 3, 5 and 6 as follows:

1. (Original) A low temperature sintering ceramic composition containing Mg, Si, Bi and Li as constituent elements, wherein the composition comprises

MgO and SiO<sub>2</sub> in sum total in the range of from 64.0 to 99.2% by mass;

Bi<sub>2</sub>O<sub>3</sub> in the range of from 0.4 to 33.0% by mass;

Li<sub>2</sub>O in the range of from 0.4 to 3.0% by mass; and

MgO and SiO<sub>2</sub> are contained in the molar ratio of from 2: 1 to 2: 3.5, at least part thereof being contained as a complex oxide of Mg and Si.

2. (Currently Amended) The low temperature sintering ceramic composition according to claim 1, wherein the composition comprises

MgO and SiO<sub>2</sub> in sum total in the range of from 75.0 to 98.0% by mass;

Bi<sub>2</sub>O<sub>3</sub> in the range of from 1.5 to 24.5% by mass; and

 $Li_2O$  in the range of from 0.5 to 3.0% by mass.

3. (Currently Amended) The low temperature sintering ceramic composition according to claim 1 [or 2], wherein the complex oxide is a forsterite system crystal phase and/or enstatite system crystal phase; and

at least part of  $Bi_2O_3$  and  $Li_2O$  is contained as a  $Bi_2O_3$ -SiO<sub>2</sub> system crystal phase and a  $Li_2O$ -SiO<sub>2</sub> system crystal phase.

- 4. (Currently Amended) The low temperature sintering ceramic composition according to claim 3, wherein the forsterite system crystal phase and/or enststite system crystal phase are is contained by 60% or more of a total volume of the ceramic.
- 5. (Currently Amended) The low temperature sintering ceramic composition according to any one of claims 1 to 4 claim 1, wherein a Qf value is 10,000 or more.
- 6. (Currently Amended) An electronic component comprising a wiring pattern on the low temperature sintering ceramic composition according to any one of claims 1 to 5 claim 1.
- 7. (Currently Amended) The electronic component according to claim 6, wherein the wiring is formed by sintering a conductive paste containing at [lease] <u>least</u> one metal selected from Ag, Au and Cu.
- 8. (Original) A method of fabricating a low temperature sintering ceramic composition comprising:

molding a raw material powder containing one or both of a mixture of MgO and  $SiO_2$  that contains MgO and  $SiO_2$  at a molar ratio in the range of from 2: 1 to 2: 3.5 and a complex oxide thereof in the range of from 64.0 to 99.2% by mass,  $Bi_2O_3$  in the range of from 0.4 to 33.0% by bass and  $Li_2O$  in the range of from 0.4 to 3.0% by mass into a predetermined shape followed by sintering at a temperature in the range of from 850 to 1000 °C.

- 9. (Original) The method according to claim 8, wherein the raw material powders are fine powders having a particle size of 2.0  $\mu$ m or less.
- 10. (New) The low temperature sintering ceramic composition according to claim 1, wherein the complex oxide is a enstatite system crystal phase; and

at least part of  $Bi_2O_3$  and  $Li_2O$  is contained as a  $Bi_2O_3$ -SiO<sub>2</sub> system crystal phase and a  $Li_2O$ -SiO<sub>2</sub> system crystal phase.

11. (New) The low temperature sintering ceramic composition according to claim 3, wherein the enststite system crystal phase is contained by 60% or more of a total volume of the ceramic.